APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/635,832	08/09/2000	Shunpei Yamazaki	07977/182002/US3413D1	6795

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EXAMINER
TOLEDO, FERNANDO L

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2823	

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Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)
Office Action Summary	09/635,832	YAMAZAKI ET AL.
	Examiner	Art Unit
	Fernando L. Toledo	2823

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE <u>3</u> MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
  Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1)☒ Responsive to communication(s) filed on <u>27 November 2006</u>.

2a)☐ This action is **FINAL**.   2b)☒ This action is non-final.

3)☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4)☒ Claim(s) *58-64,66-72,74-80,82-96,98-104,106-130 and 133-144* is/are pending in the application.

    4a) Of the above claim(s) *See Continuation Sheet* is/are withdrawn from consideration.

5)☒ Claim(s) *58,62,66,70,74,78,82,86,90,94,98,106,110,129 and 133* is/are allowed.

6)☒ Claim(s) *61,69,77,85,93,101,102,109,113,114,117,118,122,126,130,134-139 and 142-144* is/are rejected.

7)☒ Claim(s) *121,125,140 and 141* is/are objected to.

8)☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9)☐ The specification is objected to by the Examiner.

10)☐ The drawing(s) filed on _____ is/are: a)☐ accepted or b)☐ objected to by the Examiner.

    Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

    Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11)☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12)☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

    a)☒ All   b)☐ Some * c)☐ None of:

      1.☐ Certified copies of the priority documents have been received.

      2.☒ Certified copies of the priority documents have been received in Application No. <u>08/931,697</u>.

      3.☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

    * See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1)☒ Notice of References Cited (PTO-892)

2)☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)

3)☐ Information Disclosure Statement(s) (PTO/SB/08)
    Paper No(s)/Mail Date _____.

4)☐ Interview Summary (PTO-413)
    Paper No(s)/Mail Date. _____.

5)☐ Notice of Informal Patent Application

6)☐ Other: _____.

Continuation of Disposition of Claims: Claims withdrawn from consideration are 59,60,63,64,67,68,71,72,75,76,79,80,83,84,87,88,91,92,95,96,99,100,103,104,107,108,111,112,115,116,119,120,123,124,127 and 128.

DETAILED ACTION

Claim Rejections - 35 USC § 102

1.   The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the

basis for the rejections under this section made in this Office action:

> A person shall be entitled to a patent unless –
>
> (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

2.   Claims 61, 85, 93, 135 and 144 are rejected under 35 U.S.C. 102(b) as being anticipated

by Ozaki et al. (U. S. patent 5,028,976).

In re claim 61; Ozaki, in the U. S. patent 5,028,976; figures 1 – 9 and related text,

discloses at least one first transistor 2; at least one second transistor 3 over the at least one first

transistor (Figure 2); wherein each of the first and second transistors includes: a channel forming

region 17; a source region (12 or 13); a drain region (13 or 12); and a gate electrode; wherein the

first transistor is an n-channel transistor and the second transistor is a p-channel transistor

(Column 1, Lines 43 – 65), wherein several of impurity regions each includes a semiconductor

material and a first impurity element are included at least in the channel forming region of the

first transistor, wherein several of second impurity regions each comprising a semiconductor

material and a second impurity element are included at least in the channel forming region of the

second transistor, wherein each of the several impurity regions is formed in a part of the channel

region in the first transistor, wherein each of the several of second impurity regions is formed in

a part of the channel forming region in the second transistor (Column 3, Lines 55 – 65).

Ozaki does not explicitly disclose wherein the first impurity element belongs to group 13

and the second impurity element belongs to group 15. However, it is inherent that the doping

impurities will either come from group 13 for p-type doping and from group 15 for n-type

doping.

3.   In re claim 85; Ozaki discloses wherein the channel forming region, source region and

drain region includes single crystal silicon (Column 3, Lines 55 – 65).

4.   In re claim 93; Ozaki discloses wherein the second layer has an SOI structure 18.

5.   In re claim 144; Ozaki discloses wherein at least one of the first transistor and the second

transistor comprises LDD regions (Figure 2).

Claim Rejections - 35 USC § 103

6.   The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all

obviousness rejections set forth in this Office action:

> (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in
> section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are
> such that the subject matter as a whole would have been obvious at the time the invention was made to a person
> having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the
> manner in which the invention was made.

7.   Claims 113, 117, 129, 138, 139 and 142 are rejected under 35 U.S.C. 103(a) as being

unpatentable over Ozaki as applied to claims 61, 85, 93 and 135 above.

In re claims 113 and 138, Ozaki does not disclose wherein a width of the channel forming

region, a total width W_{pi} of the impurity regions, and a total width W_{pa} of regions between the

impurity regions satisfy relationships W_{pi}/W = 0.1 to 0.9, W_{pa}/W = 0.1 to 0.9, and W_{pi}/W_{pa} = 1/9 to 9.

It would have been obvious to one having ordinary skill in the art at the time the invention was made to establish a width of the channel forming region, a total width W_{pi} of the impurity regions, and a total width W_{pa} of regions between the impurity regions satisfy relationships W_{pi}/W = 0.1 to 0.9, W_{pa}/W = 0.1 to 0.9, and W_{pi}/W_{pa} = 1/9 to 9, since it has been held that where the general conditions of a claim are disclosed in the prior art, discovering the optimum or workable ranges involves only routine skill in the art. *In re Aller,* 105 USPQ 233. Note that the specification contains no disclosure of either the critical nature of the claimed width or any unexpected results arising therefrom. Where patentability is said to be based upon particular chosen width or upon another variable recited in a claim, the Applicant must show that the chosen width is critical. *In re Woodruf,* 919 F.2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990). In addition, the selection of a width of the channel forming region, a total width W_{pi} of the impurity regions, and a total width W_{pa} of regions between the impurity regions satisfy relationships W_{pi}/W = 0.1 to 0.9, W_{pa}/W = 0.1 to 0.9, and W_{pi}/W_{pa} = 1/9 to 9, is obvious because it is a matter of determining optimum process conditions by routine experimentation with a limited number of species of result effective variables. These claims are prima facie obvious without showing that the claimed ranges achieve unexpected results relative to the prior art range. In re Woodruff, 16 USPQ2d 1935, 1937 (Fed. Cir. 1990). See also In re Huang, 40 USPQ2d 1685, 1688 (Fed. Cir. 1996)(claimed ranges or a result effective variable, which do not overlap the prior art ranges, are unpatentable unless they produce a new and unexpected result

which is different in kind and not merely in degree from the results of the prior art). See also In

re Boesch, 205 USPQ 215 (CCPA) (discovery of optimum value of result effective variable in

known process is ordinarily within skill or art) and In re Aller, 105 USPQ 233 (CCPA 1995)

(selection of optimum ranges within prior art general conditions is obvious).

8.   In re claims 117 and 139, Ozaki does not disclose wherein a total width of the carrier

moving regions is within a range of 30 to 3,000 Å.

It would have been obvious to one having ordinary skill in the art at the time the

invention was made to establish a total width of the carrier moving regions is within a range of

30 to 3,000 Å, since it has been held that where the general conditions of a claim are disclosed in

the prior art, discovering the optimum or workable ranges involves only routine skill in the art.

In re Aller, 105 USPQ 233. Note that the specification contains no disclosure of either the

critical nature of the claimed width or any unexpected results arising therefrom. Where

patentability is said to be based upon particular chosen width or upon another variable recited in

a claim, the Applicant must show that the chosen width is critical. *In re Woodruf,* 919 F.2d

1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990). In addition, the selection of a width of the

channel forming region, a total width of the carrier moving regions is within a range of 30 to

3,000 Å, is obvious because it is a matter of determining optimum process conditions by routine

experimentation with a limited number of species of result effective variables. These claims are

prima facie obvious without showing that the claimed ranges achieve unexpected results relative

to the prior art range. In re Woodruff, 16 USPQ2d 1935, 1937 (Fed. Cir. 1990). See also In re

Huang, 40 USPQ2d 1685, 1688 (Fed. Cir. 1996)(claimed ranges or a result effective variable,

which do not overlap the prior art ranges, are unpatentable unless they produce a new and

unexpected result which is different in kind and not merely in degree from the results of the prior

art). See also In re Boesch, 205 USPQ 215 (CCPA) (discovery of optimum value of result

effective variable in known process is ordinarily within skill or art) and In re Aller, 105 USPQ

233 (CCPA 1995) (selection of optimum ranges within prior art general conditions is obvious).

9.   In re claims 129 and 142, Ozaki does not disclose wherein the impurity element in the

impurity regions is at a concentration of $1x10^{17}$ to $1x10^{20}$ atoms/cm^3.

It would have been obvious to one having ordinary skill in the art at the time the

invention was made to establish the impurity element in the impurity regions is at a

concentration of $1x10^{17}$ to $1x10^{20}$ atoms/cm^3, since it has been held that where the general

conditions of a claim are disclosed in the prior art, discovering the optimum or workable ranges

involves only routine skill in the art. *In re Aller,* 105 USPQ 233. Note that the specification

contains no disclosure of either the critical nature of the claimed concentration or any unexpected

results arising therefrom. Where patentability is said to be based upon particular chosen

concentration or upon another variable recited in a claim, the Applicant must show that the

chosen concentration is critical. *In re Woodruf,* 919 F.2d 1575, 1578, 16 USPQ2d 1934, 1936

(Fed. Cir. 1990). In addition, the selection of the impurity element in the impurity regions is at a

concentration of $1x10^{17}$ to $1x10^{20}$ atoms/cm^3, is obvious because it is a matter of determining

optimum process conditions by routine experimentation with a limited number of species of

result effective variables. These claims are prima facie obvious without showing that the claimed

ranges achieve unexpected results relative to the prior art range. In re Woodruff, 16 USPQ2d

1935, 1937 (Fed. Cir. 1990). See also In re Huang, 40 USPQ2d 1685, 1688 (Fed. Cir. 1996)(claimed ranges or a result effective variable, which do not overlap the prior art ranges, are unpatentable unless they produce a new and unexpected result which is different in kind and not merely in degree from the results of the prior art). See also In re Boesch, 205 USPQ 215 (CCPA) (discovery of optimum value of result effective variable in known process is ordinarily within skill or art) and In re Aller, 105 USPQ 233 (CCPA 1995) (selection of optimum ranges within prior art general conditions is obvious).

10.   Claims 69 and 77 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ozaki as applied to claims 61, 85 and 93 above, and further in view of Mei, Chi-Cu (U. S. patent 5,548,147).

In re claims 69 and 77, Ozaki does not show wherein the electric apparatus is selected from the group consisting of an LCD device, an EL device, a CL device, a TV camera, a personal computer, a car navigation apparatus, a video camera, and a portable information terminal apparatus including a cellular telephone and a mobile computer.

However, Mei, in the U. S. patent 5,548,147; figures 1 – 3J and related text, discloses that CMOS devices are conventionally used in LCD device, an EL device, a CL device, a TV camera, a personal computer, a car navigation apparatus, a video camera, and a portable information terminal apparatus including a cellular telephone and a mobile computer (Column 1, Lines 19 – 27).

It would have been obvious to one having ordinary skill in the art at the time the invention was made to use the CMOS device of Ozaki in LCD device, an EL device, a CL device, a TV camera, a personal computer, a car navigation apparatus, a video camera, and a portable information terminal apparatus including a cellular telephone and a mobile computer, since as taught by Mei, CMOS are conventionally used in such devices.

11.   Claims 97, 101, 105, 109, 136 and 137 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ozaki as applied to claims 61, 85, 93 and 135 above, and further in view of Shiue et al. (U. S. patent 5,781,445).

In re claims 97 and 101; Ozaki does not disclose wherein the impurity element belongs to group 13 (boron).

However, Shiue, in the U. S. patent 5,781,445; figures 1 – 5 and related text, discloses that for forming a p-type device boron (group 13 element) is conventionally used (Column 4, Lines 24 – 26).

It would have been obvious to one having ordinary skill in the art at the time the invention was made to use the impurity element belongs to group 13 (boron), since, as taught by Shiue, it is conventionally used to form p-type devices.

12.   In re claims 105 and 109; Ozaki does not disclose wherein the impurity element belongs to group 15 (phosphorous or arsenic).

However, Shiue discloses that for forming n-type devices, phosphorous or arsenic (group 15 elements) are conventionally used (Column 4, Lines 27 – 30).

It would have been obvious to one having ordinary skill in the art at the time the invention was made to use the impurity element belonging to group 15 (phosphorous or arsenic), since, as taught by Shiue, it is conventionally used to form n-type devices.

Claim Objections

13.   Claims 121, 125, 140 and 141 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Allowable Subject Matter

14.   Claims 58, 62, 66, 70, 74, 78, 82, 86, 90, 94, 98, 106, 110, 126, 129, 133 and 143 are allowed over the prior art of record.

Response to Arguments

15.   Applicant's arguments filed 27 November 2006 have been fully considered but they are not persuasive for the following reasons.

16.   Applicant again contests that the channel region of Ozaki does not have impurities of the opposite type (i.e. that the n-channel region has p-type impurities and that the p-channel region has n-type impurities). Examiner respectfully submits that, although Ozaki does not actively teaches the aforementioned limitation, Ozaki implicitly teaches such limitation since a n-channel transistor would have p-type doping for the source and drain, and these impurities would diffuse

to some extent into the channel region, since diffusion of impurities are governed by Fick's Law, which states that molecules (in this case, p-type impurities) from a higher concentration region (source and drain) would move to a lower concentration region (channel region) in order to establish a balance between the two concentrations as seen by the explanations of Levine in the textbook Physical Chemistry pages 465 – 467 and Wolf and Tauber Silicon Processing for the VLSI Era Volume 1: Process Technology pages 242 – 248. The same would happen for the p-type channel transistor in that it would have n-type doping for the source and drain and these impurities would diffuse, to some extent, into the channel region. Therefore, the 35 USC §102 and §103 rejections stand and are considered proper.
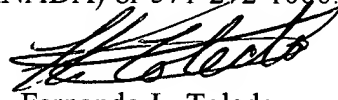
Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Fernando L. Toledo whose telephone number is 571-272-1867. The examiner can normally be reached on Mon-Fri 8am-4:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew Smith can be reached on 571-272-1907. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Fernando L. Toledo
Primary Examiner
Art Unit 2823

flt
21 May 2007